



MCH6341

Power MOSFET -30V, 59mΩ, -5A, Single P-Channel

ON Semiconductor®

<http://onsemi.com>

Features

- Low $R_{DS(on)}$
- Pb-free and RoHS Compliance
- 4V drive
- ESD diode-Protected gate

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

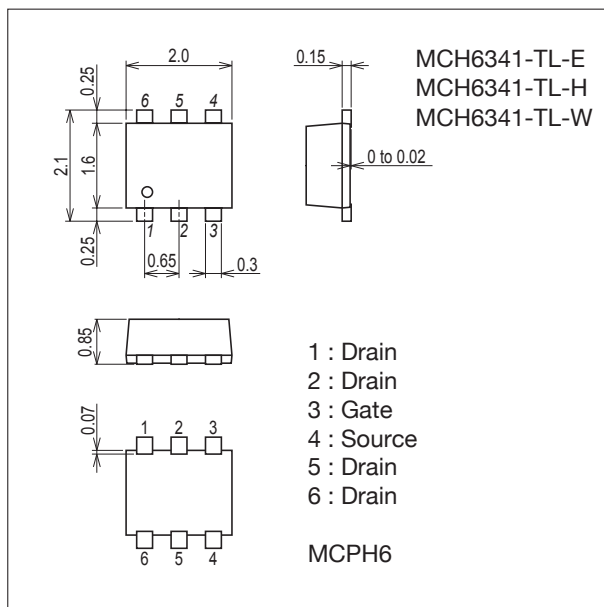
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-30	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		-5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-20	A
Power Dissipation	P_D	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Package Dimensions

unit : mm (typ)

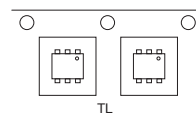
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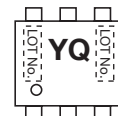
Product & Package Information

- Package : MCH6341
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

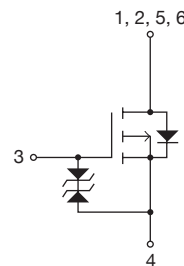
Packing Type : TL



Marking



Electrical Connection



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

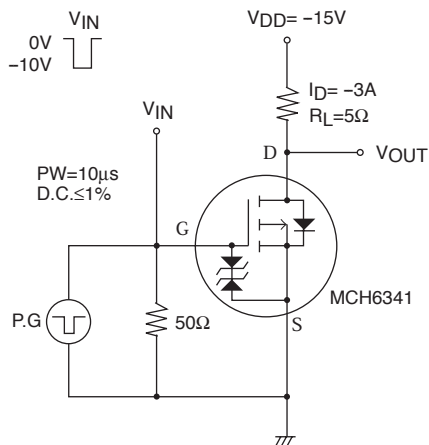
MCH6341

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-3A	2.8	4.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-3A, V _{GS} =-10V		45	59	mΩ
	R _{DS(on)2}	I _D =-1.5A, V _{GS} =-4.5V		71	100	mΩ
	R _{DS(on)3}	I _D =-1.5A, V _{GS} =-4V		82	115	mΩ
Input Capacitance	C _{iss}			430		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		105		pF
Reverse Transfer Capacitance	C _{rss}			75		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7.5		ns
Rise Time	t _r			26		ns
Turn-OFF Delay Time	t _{d(off)}			45		ns
Fall Time	t _f			35		ns
Total Gate Charge	Q _g				10	
Gate-to-Source Charge	Q _{gs}	V _{DS} =-15V, V _{GS} =-10V, I _D =-5A		2.0		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			2.5		nC
Forward Diode Voltage	V _{SD}	I _S =-5A, V _{GS} =0V		-0.87	-1.5	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH6341-TL-E	MCPH6	3,000pcs./reel	Pb Free
MCH6341-TL-H	MCPH6	3,000pcs./reel	Pb Free and Halogen Free
MCH6341-TL-W	MCPH6	3,000pcs./reel	Pb Free and Halogen Free

